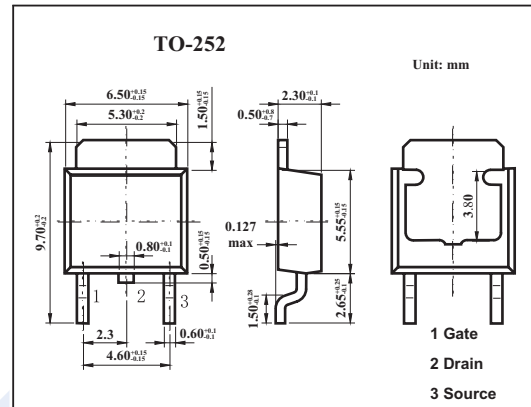
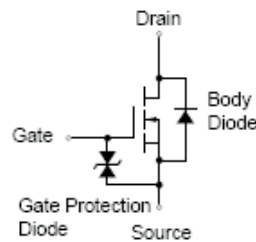


MOS Field Effect Transistor 2SK2415

■ Features

- Low On-Resistance
 $R_{DS(on)1} = 0.10 \Omega$ MAX. (@ $V_{GS} = 10 V, I_D = 4.0 A$)
 $R_{DS(on)2} = 0.15 \Omega$ MAX. (@ $V_{GS} = 4 V, I_D = 4.0 A$)
- Low C_{iss} $C_{iss} = 570$ pF TYP.



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{DS}	60	V
Gate to source voltage	V_{GS}	± 20	V
Drain current	I_D	± 8.0	A
	I_{DP}^*	± 32	A
Power dissipation	P_D	20	W
Channel temperature	T_{ch}	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

* $PW \leq 10 \mu s, Duty Cycle \leq 1\%$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain cut-off current	I_{DSS}	$V_{DS}=60V, V_{GS}=0$			10	μA
Gate leakage current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0$			± 10	μA
Gate to source cutoff voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	1.0	1.6	2.0	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=10V, I_D=4A$	5.0	8.4		S
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=4A$		0.07	0.10	Ω
		$V_{GS}=4V, I_D=4A$		0.10	0.15	Ω
Input capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0, f=1MHz$		570		pF
Output capacitance	C_{oss}			290		pF
Reverse transfer capacitance	C_{rss}			75		pF
Turn-on delay time	t_{on}				5	ns
Rise time	t_r	$I_D=4A, V_{GS(on)}=10V, R_G=10\Omega, V_{DD}=30V$		60		ns
Turn-off delay time	t_{off}			75		ns
Fall time	t_f				40	ns